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Ga Segregation Impact on $Al_{0.35}Ga_{0.65}As/GaAs$ SQW Energy Bandgap

Vahid R. Yazdanpanah[1*], Pouria Hosseinzadeh[1] and Sattar Mirzakuchaki[1]

[1]*School of Electrical Engineering, Iran University of Science and Technology, Narmak, Tehran, Iran.*

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ABSTRACT

This paper studies the impact of Ga segregation on energy bandgap of $Al_{0.35}Ga_{0.65}As/GaAs$ single quantum well system as a function of growth temperature and growth rate using kinetic model and Empirical Tight Binding method. This work indicates amount of red shift can be expected when the growth temperature changes from 500 ^oC to 710 ^oC and expected amount of blue shift ct when growth rate increases from 0.1 ML/s to 1 ML/s because of Ga segregation in $Al_{0.35}Ga_{0.65}As/GaAs$ SQW system. This paper suggests that in order to compensate for the Ga segregation and keep the energy bandgap of $Al_{0.35}Ga_{0.65}As/GaAs$ SQW system at 1.53 eV equivalent to 808 nm wavelength, the authors need to reduce 4 ML of the GaAs QW thickness from ideal case when there is no Ga segregation.

Keywords: Gallium Segregation, Growth Temperature, Growth Rate, Energy Bandgap, Kinetic Model, Empirical Tight Binding Method.

1. INTRODUCTION

High-performance optoelectronic devices such as lasers, light emitting diodes (LED), solar cells and infrared detectors can be fabricated based on the complex quantum structures of III-V semiconductors. Quantum structures such as quantum wells (QW), quantum dots (QD), and super-lattices can be grown with high quality using molecular beam epitaxy (MBE). However, abrupt interface between different semiconductor compounds is a challenge due to interfacial atomic segregation [1,2].

For low growth temperatures (for example 600^o C in AlGaAs/GaAs system), atomic arrangement in the crystal is determined by surface or near-surface processes and atoms have less chance to rearrange after burial under upcoming layers. However, due to the surface mobility, atoms can displace on the growing surface. Higher growth temperature leads to the increase of the surface mobility that can result in smoother surface. However, it also causes the so-called "surface segregation" that is the exchange between the sub-layer atoms with the impinging atoms on the growing surface. Atomic surface segregation is driven by the differences in their binding and elastic energies [3]. Several experimental and theoretical studies indicate that both group III and V atoms with weaker bond strength and elastic energy segregate to the surface [2-7]. For instance, on the well-known AlGaAs/GaAs QW system, theoretical and experimental results show Ga segregation in AlGaAs layer that can cause a composition asymmetry at the normal interface for both AlGaAs/GaAs and GaAs/AlGaAs growths [8-14]. The composition asymmetry at the interfaces results in the change of the energy band alignment of the quantum structures, which alters the optoelectronic properties. Therefore, to design an optoelectronic device based on the III-V semiconductor structures, it is important to predict and compensate the

[*]Corresponding Author: *yazdanv@iust.ac.ir*

concentration profile change due to the segregating of atoms. In this work, kinetic model (KM) and empirical tight-binding method (ETBM) were used to predict and compensate Ga segregation impact on $Al_{0.35}Ga_{0.65}As/GaAs$ SQW energy bandgap.

2. THEORETICAL COMPUTATION

2.1 Atomic Concentration Profile

Various theoretical atomic segregation approaches have been proposed to predict the atomic concentration profile such as kinetic Monte Carlo (KMC) and KM [3, 15-17]. Using KMC, the growth processes can be simulated based on the short-range surface diffusion of adatoms which exponentially depends on the activation energy for the surface diffusion [15]. Consequently, the concentration of constituent atoms can be calculated for each monolayer (ML) [15]. On the other hand, the KM is a kinetic thermodynamic model, where the atomic concentration profile is calculated based on the probability of the exchange of atoms on the surface with the atoms in the underlying layer [3].

The KM can simulate a layer by layer growth mode of an $A_xB_{1-x}C$ of group III-V alloy on a BC substrate; in which A and B are the group-III elements and C belongs to the group-V elements. In KM, the exchange is considered between the atoms on the uppermost layer (surface) and in one layer below the surface (bulk). The exchange process occurs when atom-A takeover atom-B site by overcoming a barrier energy of $E_{A/B}{}^{b\rightarrow s}$ to move from the bulk to the surface. The inverse exchange also happens when atom-A on the surface overcomes the barrier energy of $E_{A/B}{}^{s\rightarrow b}$ and moves into the bulk. The exchange rate, therefore, is given by [3, 16]:

$$P_{A/B}^{b\rightarrow s} = v\, e^{\left(\frac{-E_{A/B}^{b\rightarrow s}}{k_B T}\right)} \tag{1}$$

and the inverse exchange rate from surface to bulk is given by:

$$P_{A/B}^{s\rightarrow b} = v\, e^{\left(\frac{-E_{A/B}^{s\rightarrow b}}{k_B T}\right)} \tag{2}$$

Where, v = 10^{13}Hz is the atomic vibration frequency, T is the growth temperature, and k_B is the Boltzmann constant. Therefore, segregation driving force (E_s) is determined as:

$$E_s = E_{A/B}^{s\rightarrow b} - E_{A/B}^{b\rightarrow s} \tag{3}$$

Assuming that the segregation is only due to the exchange processes, the balance of the incoming to and leaving atoms from the surface gives the evaluation of the number of atom-A on the surface. Hence [3]:

$$\frac{dX_A^s(t)}{dt} = \Phi_A + P_{A/B}^{b\rightarrow s} X_A^b(t) X_B^s(t) - P_{A/B}^{s\rightarrow b} X_A^s(t) X_B^b(t) \tag{4}$$

In Equation 4, Φ_A is the impinging flux of atom-A, $X^s{}_A(t)$ and $X^b{}_A(t)$ are the concentration of atom-A at time t on the surface or in the bulk, respectively. On the other hand, due to the mass conservation for atoms and the fact that $X^b{}_A(t) + X^b{}_B(t) = 1$ at any time, the following conditions must be achieved [3, 16]:

$$X_A^s(t) + X_A^b(t) = X_A^s(0) + X_A^b(0) + \Phi_A t \tag{5}$$

$$X_A^S(t) + X_B^S(t) = X_A^S(0) + X_B^S(0) + (\Phi_A + \Phi_B)t \quad (6)$$

Using Equations 4 to Equation 6, atomic concentration profile for different growth conditions can be predicted.

Based on KM, barrier energy of atoms and growth conditions such as growth temperature and growth rate, can alter the segregation length which is the maximum Ga segregation length. For example, In segregation length in AlSb/InSb system has been reported to be 15 ML at growth temperature of 520°C with a growth rate of 0.5 ML/s [18].

In this work, the authors calculated Al concentration profile for 19 MLs of GaAs sandwiched between 39 MLs of $Al_{0.35}Ga_{0.65}As$ SQW at different growth conditions. This SQW system has 0.04% mismatch which makes it a good candidate for MBE 2D growth.

Figure 1 shows the calculated Al concentration profile for both non-segregated and segregated $Al_{0.35}Ga_{0.65}As$/GaAs at a growth temperature of 710 °C and a growth rate of 0.1 ML/s.

The figure shows that Ga segregation has no effect on GaAs profile, while it alters the AlGaAs profile. Based on the calculation, the segregation length in AlGaAs layer is expected to be 7 MLs at growth temperature of 710 °C with a growth rate of 0.1 ML/s, which is much smaller than in segregation length in similar systems.

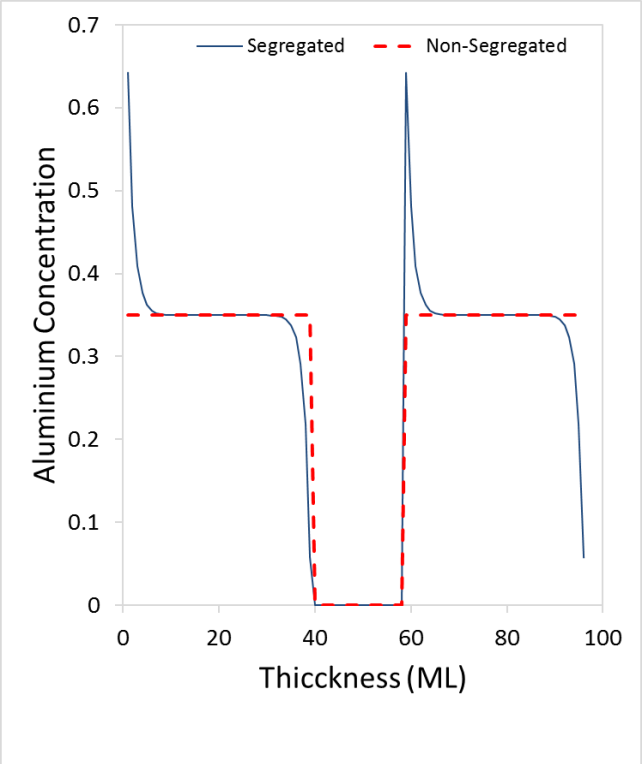

Figure 1. Al concentration profile for both non-segregated (dashed line) and segregated (solid line) for 19 MLs of GaAs sandwiched between 39 MLs of $Al_{0.35}Ga_{0.65}As$ SQW at a growth temperature of 710 °C and growth rate of 0.1 ML/s.

Based on KM, reducing growth temperature and/or increasing growth rate can reduce Ga segregation and causes an atomic concentration profile closer to non-segregated profile. However, lower growth temperature and higher growth rate leads to rougher interfaces and broaden energy band gap, which is not desirable. This is the reason the segregation effect at

high temperature can be compensated by readjusting the energy bandgap by changing the GaAs well thickness.

2.2 Energy Bandgap Modeling

For energy bandgap calculation, ETBM was used considering the spin-orbit, first-nearest-neighbor and sp^3s^* orbitals which is more accurate modeling method compared with other methods such as k.p especially when the thickness variation is only few MLs. Similar to previous work, it was assumed that $Al_{0.35}Ga_{0.65}As$ Hamiltonian matrix elements have the same value as the corresponding matrix elements in the AlAs or GaAs bulk after considering corrections for ternary materials. Therefore, the ternary ETBM numerical fitting parameters were obtained from AlAs and GaAs bulk energy band-structures [19-22].

3. RESULTS AND DISCUSSION

The authors started from a unite cell consists of 39 MLs of $Al_{0.35}Ga_{0.65}As$ and 19 MLs of GaAs. Considering 5 states of sp^3s^* for each atom with both spin-up and spin-down states, the Hamiltonian for such a unit cell become a 1160 X 1160 elements matrix. Based on this Hamiltonian, for a non-segregated material (ideal case), the predicted bandgap energy was expected to be 1.53 eV which was equivalent to a wavelength of 808 nm.

When Ga segregation was considered, the $Al_{0.35}Ga_{0.65}As$ interfaces were no longer stay abrupt. The deformed interfaces modify the $Al_{0.35}Ga_{0.65}As$ barrier height and alters the energy bandgap and optoelectronic properties of the desired quantum structure. The ETB energy bandgap modeling shows that the Ga segregation in $Al_{0.35}Ga_{0.65}As/GaAs$ system causes a 0.1 eV redshift and decreases the energy bandgap from 1.53 eV to about 1.43 eV at a growth temperature of 710 ^{o}C and growth rate of 0.1 ML/s.

Figure 2 shows growth temperature and growth rate dependencies of the $Al_{0.35}Ga_{0.65}As/GaAs$ calculated energy bandgap due to the Ga segregation. From that, it can be seen that increasing growth temperature results on a redshift. At high growth rate of 1 ML/s, increasing the temperature from 500 ^{o}C to 710 ^{o}C results on <0.04 eV redshift; while, at low growth rate of 0.1 ML/s, it causes greater redshift of about 0.1 eV. This is because, when the growth temperature was increased, the Ga segregation energy increased too. Therefore, the segregation rate increased and energy bandgap of the system decreased.

Figure 2 reveals that in a range of 500-710 ^{o}C, increasing growth rate reduces the Ga segregation and increases the energy bandgap of the system. At low growth temperatures, the growth rate has minimal effect on the energy bandgap. As the temperature increases from 500 ^{o}C to 710 ^{o}C, growth rate effect on energy bandgap becomes more significant. For example, at a growth temperate of 500 ^{o}C, altering growth rate 0.1-1 ML/s can result in <0.01 eV; whereas, the same growth rate range can alter the energy bandgap 0.07 eV at 710 ^{o}C. This is because, when the growth rate wasincreased, the time that Ga needed for segregation decreased. Therefore, the segregation rate decreased and as a result of less energy bandgap variation.

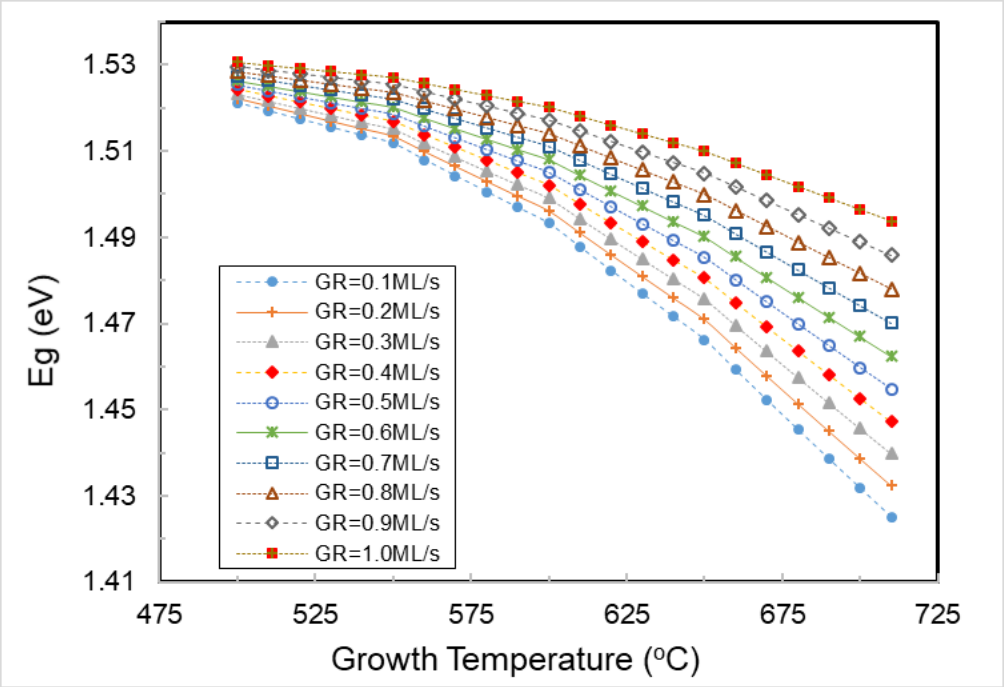

Figure 2. The growth temperature and growth rate dependencies of the $Al_{0.35}Ga_{0.65}As$/GaAs calculated energy bandgap due to the Ga segregation.

At high growth temperature and/or low growth rate, Ga segregation can still be compensated by altering the GaAs QW thickness. Figure 3 shows calculated energy bandgap at a growth temperature of 710 °C and a growth rate of 1ML/s for different GaAs QW thicknesses. From Figure 3, it can be seen that by reducing 4 ML of the GaAs QW thickness down to 15 ML, 1.53 eV bandgap can be achieved for a wavelength of about 808nm, which is close to reported experimental results on the similar systems [23, 24].

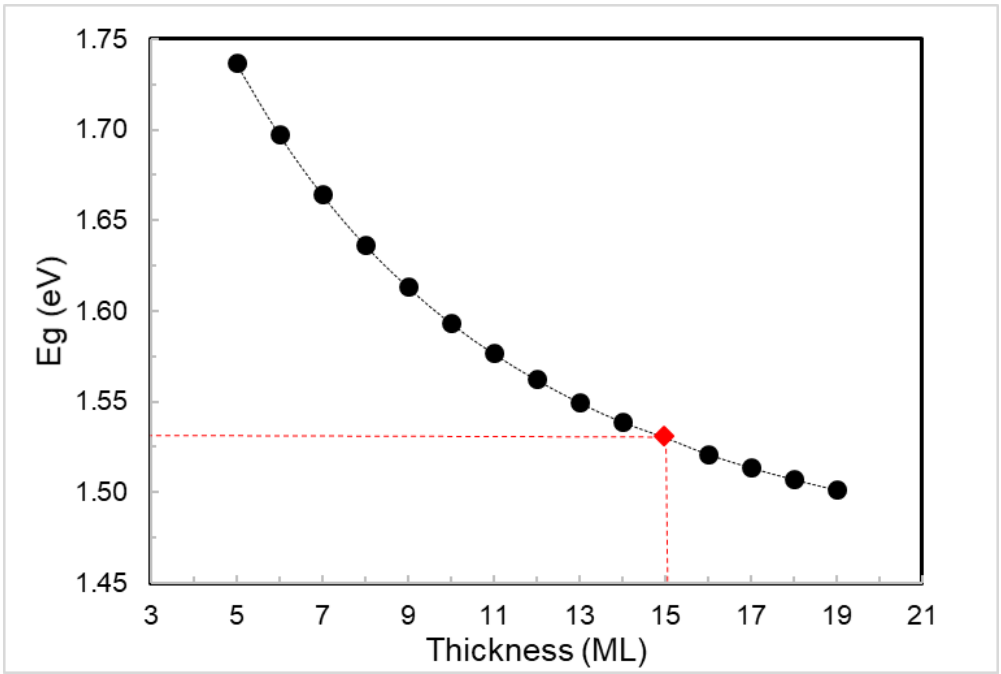

Figure 3. $Al_{0.35}Ga_{0.65}As$/GaAs calculated energy bandgap variation for different GaAs thicknesses at a growth temperature of 710 °C and growth rate of 1ML/s with considering Ga segregation.

Similarly, other researchers can use the same method to modify the energy bandgap at different growth temperature and growth rates.

4. CONCLUSION

As a conclusion, Kinetic model and ETBM were used to study effect of Ga segregation on energy bandgap of $Al_{0.35}Ga_{0.65}As/GaAs$ SQW system at different growth temperatures (500-710 ^{o}C) and growth rates (0.1-1 ML/s).

This study shows that increasing growth temperature will increase the Ga segregation and causes a redshift; whereas, increasing growth rate will decreases the Ga segregation and causes a blueshift. It was predicted thagt in order to compensate for Ga segregation and keep the energy bandgap of $Al_{0.35}Ga_{0.65}As/GaAs$ SQW system at 1.53 eV at high growth temperature of 710 ^{o}C and growth rate of 1 ML/s, 4 ML of the GaAs QW thickness needs to be reduced compared with when there is no Ga segregation.

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